

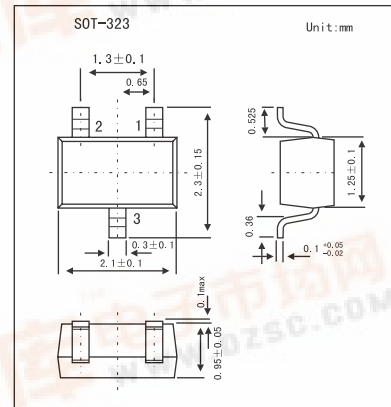
SMD Type Diodes

HIGH SPEED SWITCHING SILICON EPITAXIAL DOUBLE DIODE

1SS303

■ Features

- Low capacitance: Ct = 2.5 pF TYP.
- High speed switching: trr = 4.0 ns MAX.
- Wide applications including switching, limiter, clipper.
- Double diode configuration assures economical use.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V _{RM}	75	V
DC Reverse Voltage	V _R	50	V
Surge Current (1 μs) Note 1	I _{FSM}	6.0	A
Surge Current (1 μs)	I _{FSM}	4.0	A
Peak Forward Current Note 1	I _{FM}	450	mA
Peak Forward Current	I _{FM}	300	mA
Average Rectified Current (Note 1)	I _O	150	mA
Average Rectified Current	I _O	100	mA
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction to Ambient (Note 1)	R _{th(j-a)}	1.0	°C/mW
Junction to Ambient	R _{th(j-a)}	0.85	°C/mW

Note

1. Both diodes loaded simultaneously.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V _{F(1)}	I _F = 1 mA		0.72	1.0	V
	V _{F(2)}	I _F = 50 mA		0.88	1.1	
	V _{F(3)}	I _F = 100 mA		1.0	1.2	
Reverse current	I _{R(1)}	V _R = 50 V			0.1	μA
Capacitance	C _t	V _R = 0, f = 1.0 MHz		2.5	4.0	pF
Reverse recovery time	trr				4.0	ns

■ Marking

Marking	A4
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